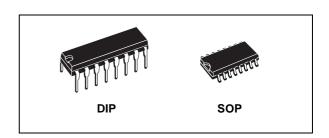


## 4-BIT MAGNITUDE COMPARATOR

- QUIESCENT CURRENT SPECIFIED UP TO 20V
- STANDARD B-SERIES OUTPUT DRIVE
- EXPANSION TO 8-16....4 N BITS BY CASCADING UNIT
- MEDIUM SPEED OPERATION: COMPARES TWO 4-BIT WORDS IN 250ns (Typ.) at 10V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT  $I_1 = 100$ nA (MAX) AT  $V_{DD} = 18$ V  $T_A = 25$ °C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



#### **ORDER CODES**

PACKAGE	TUBE	T&R
DIP	HCF4063BEY	
SOP	HCF4063BM1	HCF4063M013TR

#### **DESCRIPTION**

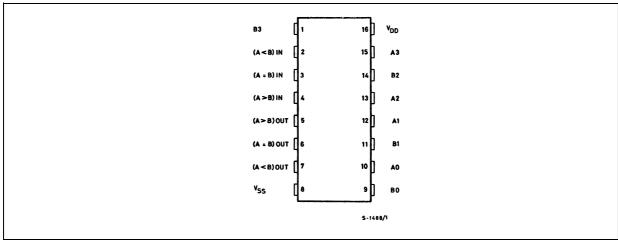
The HCF4063B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4063B is a low power 4-bit magnitude comparator designed for use in computer and logic applications that require the comparison of two 4-bit words. This logic circuit determines whether one 4-bit word (Binary or BCD) is "less than", "equal to" or "greater than" a second 4 bit word. The HCF4063B has eight comparing inputs (A3, B3 through A0, B0), three outputs (A<B, A=B, A>B) and three cascading inputs (A<B, A=B, A>B)

that permit system s designers to expand the comparator function to 8, 12, 16...4N bits. When a single HCF4063B is used the cascading inputs are connected as follows:

(A < B) = low, (A = B) = high, (A > B) = low.

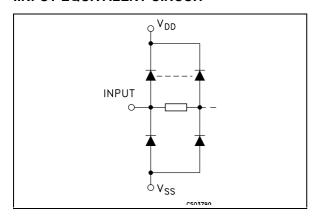
For words longer than 4 bits, HCF4063B device may be cascaded by connecting the outputs of the less-significant comparator to the corresponding cascading inputs of the more significant comparator. Cascading inputs (A<B, A=B, and A>B) on the least significant comparator are connected to a low, a high, and a low level, respectively.

#### **PIN CONNECTION**



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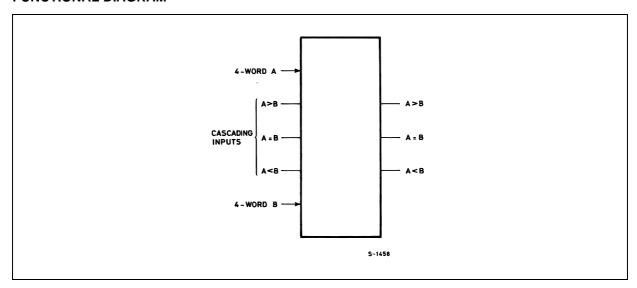
#### **IINPUT EQUIVALENT CIRCUIT**



#### **PIN DESCRIPTION**

(F.		
PIN No	SYMBOL	NAME AND FUNCTION
10, 12, 13, 15	A0 to A3	Word A Inputs
9, 11, 14, 1	B0 to B3	Word B Inputs
5, 6 ,7	A>B, A=B, A <b< td=""><td>Outputs</td></b<>	Outputs
4, 3, 2	A>B, A=B, A <b< td=""><td>Cascading Inputs</td></b<>	Cascading Inputs
8	$V_{SS}$	Negative Supply Voltage
16	$V_{DD}$	Positive Supply Voltage

## **FUNCTIONAL DIAGRAM**

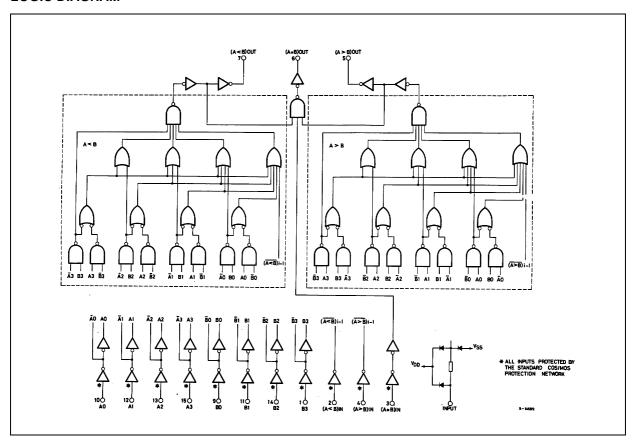


### **TRUTH TABLE**

	INPUTS								OUTDUTO			
	COMP	ARING		С	OUTPUTS							
A3, B3	A3, B3 A2, B2 A1, B1 A0, B0				A=B	A>B	A <b< th=""><th>A=B</th><th>A&gt;B</th></b<>	A=B	A>B			
A3 > B3	Х	Х	Х	Х	Х	Х	L	L	Н			
A3 = B3	A2 > B2	Х	Х	Х	Х	Х	L	L	Н			
A3 = B3	A2 = B2	A1 > B1	Х	Х	Х	Х	L	L	Н			
A3 = B3	A2 = B2	A1 = B1	A0 > B0	Х	Х	Х	L	L	Н			
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	Н	L	L	Н			
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	Н	L	L	Н	L			
A3 = B3	A2 = B2	A1 = B1	A0 = B0	Н	L	L	Н	L	L			
A3 = B3	A2 = B2	A1 = B1	A0 < B0	Х	Х	Х	Н	L	L			
A3 = B3	A2 = B2	A1 < B1	Х	Х	Х	Х	Н	L	L			
A3 = B3	A2 < B2	Х	Х	Х	Х	Х	Н	L	L			
A3 < B3	Х	X	X	Х	Х	Х	Н	L	L			

X : Don't Care

#### **LOGIC DIAGRAM**



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	-0.5 to +22	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>I</sub>	DC Input Current	± 10	mA
P <sub>D</sub>	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T <sub>op</sub>	Operating Temperature	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V<sub>SS</sub> pin voltage.

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	3 to 20	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

#### **DC SPECIFICATIONS**

		Test Condition				Value							
Symbol	Parameter	VI	v <sub>o</sub>	l <sub>o</sub>	(μ <b>A</b> ) (V)	T <sub>A</sub> = 25°C			-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	(μ <b>A</b> )		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Current	0/5			5		0.04	5		150		150	
		0/10			10		0.04	10		300		300	
	0/15			15		0.04	20		600		600	μΑ	
		0/20			20		0.08	100		3000		3000	
$V_{OH}$	High Level Output	0/5		<1	5	4.95			4.95		4.95		
	Voltage	0/10		<1	10	9.95			9.95		9.95		V
		0/15		<1	15	14.95			14.95		14.95		
$V_{OL}$	Low Level Output	5/0		<1	5		0.05			0.05		0.05	
	Voltage	10/0		<1	10		0.05			0.05		0.05	V
		15/0		<1	15		0.05			0.05		0.05	
$V_{IH}$	High Level Input		0.5/4.5	<1	5	3.5			3.5		3.5		V
	Voltage		1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
$V_{IL}$	Low Level Input		4.5/0.5	<1	5			1.5		1.5		1.5	
	Voltage		9/1	<1	10			3		3		3	V
			13.5/1.5	<1	15			4		4		4	
I <sub>OH</sub>	Output Drive	0/5	2.5	<1	5	-1.36	-3.2		-1.1		-1.1		
	Current	0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		mA
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		1117 (
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
$I_{OL}$	Output Sink	0/5	0.4	<1	5	0.44	1		0.36		0.36		
Current	Current	0/10	0.5	<1	10	1.1	2.6		0.9		0.9		mΑ
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I <sub>I</sub>	Input Leakage Current	0/18	Any In	put	18		±10 <sup>-5</sup>	±0.1		±1		±1	μΑ
Cl	Input Capacitance		Any In	put			5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with  $V_{DD}$ =5V, 2V min. with  $V_{DD}$ =10V, 2.5V min. with  $V_{DD}$ =15V

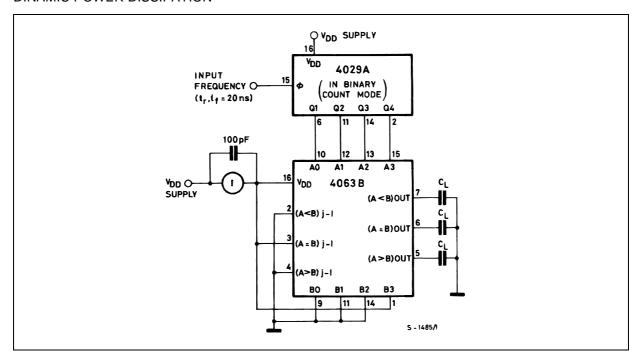
# $\textbf{DYNAMIC ELECTRICAL CHARACTERISTICS} \; (\textbf{T}_{amb} = 25^{\circ} \textbf{C}, \;\; \textbf{C}_{L} = 50 \text{pF}, \; \textbf{R}_{L} = 200 \text{K}\Omega, \;\; \textbf{t}_{r} = \textbf{t}_{f} = 20 \; \text{ns})$

Symbol	Parameter		Test Condition	'	Unit		
Symbol	Parameter	V <sub>DD</sub> (V)		Min.	Тур.	Max.	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	5			625	1250	
		10	Comparing Inputs to Outputs		250	500	ns
		15			175	350	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	5			500	1000	
		10	Cascading Inputs to Outputs		200	400	ns
		15			140	280	
t <sub>THL</sub> t <sub>TLH</sub>	Transition Time	5			100	200	
		10			50	100	ns
		15			40	80	

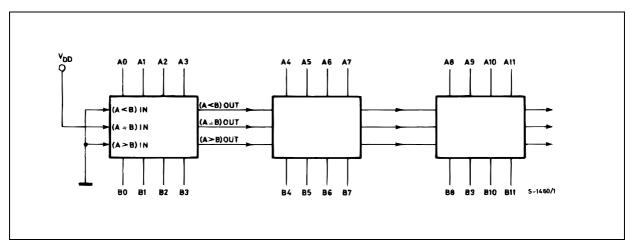
(\*) Typical temperature coefficient for all  $V_{DD}$  value is 0.3 %/°C.

#### **TYPICAL APPLICATIONS**

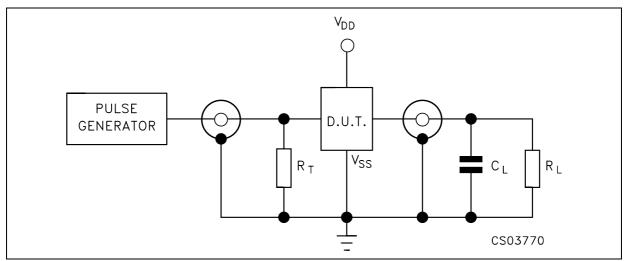
#### **DINAMIC POWER DISSIPATION**



#### TYPICAL SPEED CHARACTERISTICS OF A 12-BIT COMPARATOR

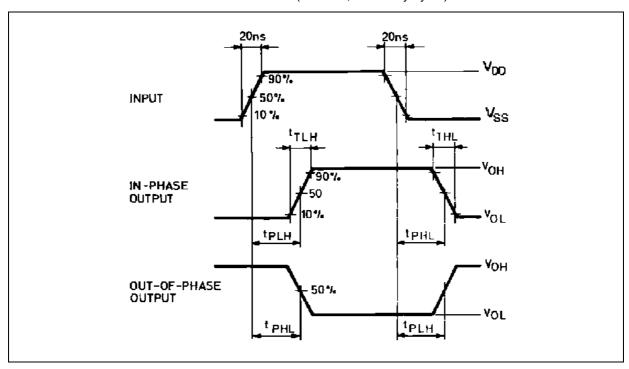


#### **TEST CIRCUIT**



 $C_L$  = 50pF or equivalent (includes jig and probe capacitance)  $R_L$  = 200KΩ  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50Ω)

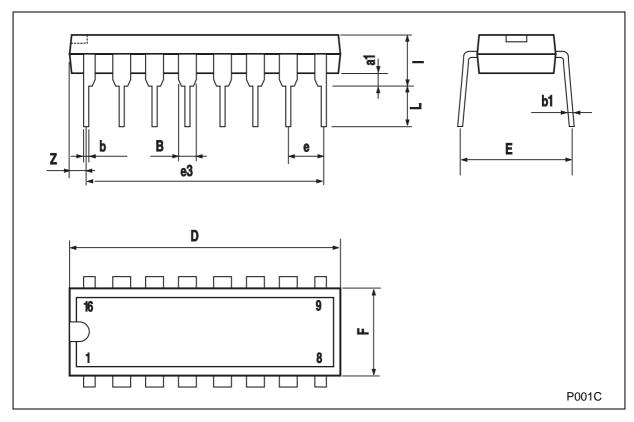
## WAVEFORM: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



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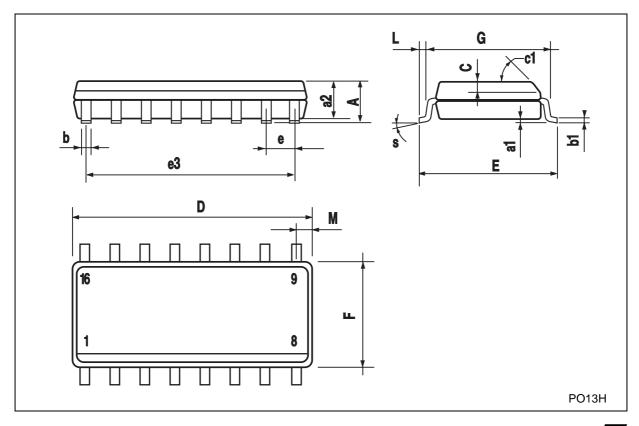
# Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.		mm.				
Dilvi.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



## **SO-16 MECHANICAL DATA**

DIM		mm.		inch					
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
Α			1.75			0.068			
a1	0.1		0.2	0.003		0.007			
a2			1.65			0.064			
b	0.35		0.46	0.013		0.018			
b1	0.19		0.25	0.007		0.010			
С		0.5			0.019				
c1			45°	(typ.)	•				
D	9.8		10	0.385		0.393			
Е	5.8		6.2	0.228		0.244			
е		1.27			0.050				
e3		8.89			0.350				
F	3.8		4.0	0.149		0.157			
G	4.6		5.3	0.181		0.208			
L	0.5		1.27	0.019		0.050			
М			0.62			0.024			
S			8° (	max.)	•	•			



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